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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/811,107	03/26/2004	Hironobu Fukui	2102475-992050	9214
	7590 05/03/2007 UDNICK GRAY CARY U	EXAMINER		
2000 UNIVER	SITY AVENUE	LEWIS, MONICA		
E. PALO ALTO, CA 94303-2248			ART UNIT	PAPER NUMBER
			2822	
			,	
			MAIL DATE	DELIVERY MODE
			05/03/2007	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(s)	
	10/811,107	FUKUI, HIRONOBU	
Office Action Summary	Examiner	Art Unit	
	Monica Lewis	2822	
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the o	correspondence address	
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period was realiure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tinuity will apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	N. mely filed the mailing date of this communication. ED (35 U.S.C. § 133).	
Status			
Responsive to communication(s) filed on 12 Fe This action is FINAL. 2b) ☑ This Since this application is in condition for allowar closed in accordance with the practice under E	action is non-final. nce except for formal matters, pro		
Disposition of Claims		,	
 4) Claim(s) 1-20 is/are pending in the application. 4a) Of the above claim(s) 17-20 is/are withdraw 5) Claim(s) is/are allowed. 6) Claim(s) is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) 1-16 are subject to restriction and/or expressions. 	n from consideration.		
Application Papers			
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) access applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Examine	epted or b) objected to by the drawing(s) be held in abeyance. Se ion is required if the drawing(s) is ob	e 37 CFR 1.85(a). ojected to. See 37 CFR 1.121(d).	
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the prior application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Applicat ity documents have been receive I (PCT Rule 17.2(a)).	ion No ed in this National Stage	
·			
Attachment(s)	<u></u>		
Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948)	4) Interview Summary Paper No(s)/Mail D		
Notice of Dratsperson's Patent Brawing Review (PTO-948) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date	5) Notice of Informal F		

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DETAILED ACTION

1. This restriction is in response to the election filed February 12, 2007.

Election/Restrictions

2. This application contains claims directed to the following patentably distinct species of the claimed invention:

Embodiment I (Claims 1-4), directed to a semiconductor having a metal oxide MOS transistor comprising an additional load capacitance that is formed at a part of the semiconductor device which is vulnerable to soft errors wherein the part that is vulnerable to soft errors is a first diffusion layer region and the first diffusion layer region is at least a part of diffusion layer regions formed in the MOS transistor structure and is connected to neither a power supply nor a ground; Embodiment II (Claims 1 and 5), directed to a semiconductor having a metal oxide MOS transistor comprising an additional load capacitance that is formed at a part of the semiconductor device which is vulnerable to soft errors wherein the MOS structure includes at least a n-type MOS transistor;

Embodiment III (Claims 1 and 6), directed to a semiconductor having a metal oxide MOS transistor comprising an additional load capacitance that is formed at a part of the semiconductor device which is vulnerable to soft errors wherein the MOS is a SRAM having a flip-flop circuit that comprises a plurality of n-type MOS transistors and a plurality of p-type MOS transistors;

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Embodiment IV (Claims 1 and 7), directed to a semiconductor having a metal oxide MOS transistor comprising an additional load capacitance that is formed at a part of the semiconductor device which is vulnerable to soft errors wherein the MOS includes at least a n-type MOS and a p-type MOS transistor;

Embodiment V (Claims 1 and 8), directed to a semiconductor having a metal oxide MOS transistor comprising an additional load capacitance that is formed at a part of the semiconductor device which is vulnerable to soft errors wherein the MOS is a SPAM having a flip-flop circuit that comprises a plurality of n-type MOS transistors and a plurality of p-type MOS transistors;

Embodiment VI (Claims 9-12), directed to a semiconductor having a metal oxide MOS transistor comprising a buried well region that is formed at a part of the semiconductor device which is vulnerable to soft errors wherein the part is vulnerable to soft errors is a first diffusion layer region, and the first diffusion layer region is at least a part of diffusion layer regions formed in the MOS type transistor structure and is connected to neither power supply nor a ground; Embodiment VII (Claims 9 and 13), directed to a semiconductor having a metal oxide MOS transistor comprising a buried well region that is formed at a part of the semiconductor device which is vulnerable to soft errors wherein the MOS structure includes at least a n-type MOS transistor;

Embodiment VIII (Claims 9, 14 and 16), directed to a semiconductor having a metal oxide MOS transistor comprising a buried well region that is formed at a part of the semiconductor device which is vulnerable to soft errors wherein the

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MOS is a SRAM having a flip-flop circuit that comprises a plurality of n-type MOS transistors and a plurality of p-type MOS transistors; and Embodiment IX (Claims 9 and 15), directed to a semiconductor having a metal oxide MOS transistor comprising a buried well region that is formed at a part of the semiconductor device which is vulnerable to soft errors comprises a plurality of n-type MOS transistors and a plurality of p-type MOS transistors.

Applicant is required under 35 U.S.C. 121 to elect a single disclosed species for prosecution on the merits to which the claims shall be restricted if no generic claim is finally held to be allowable.

Applicant is advised that a reply to this requirement must include an identification of the species that is elected consonant with this requirement, and a listing of all claims readable thereon, including any claims subsequently added. An argument that a claim is allowable or that all claims are generic is considered nonresponsive unless accompanied by an election.

Upon the allowance of a generic claim, applicant will be entitled to consideration of claims to additional species which are written in dependent form or otherwise include all the limitations of an allowed generic claim as provided by 37 CFR 1.141. If claims are added after the election, applicant must indicate which are readable upon the elected species. MPEP § 809.02(a).

Should applicant traverse on the ground that the species are not patentably distinct, applicant should submit evidence or identify such evidence now of record showing the species to be obvious variants or clearly admit on the record that this is the case. In either instance, if the

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examiner finds one of the inventions unpatentable over the prior art, the evidence or admission

may be used in a rejection under 35 U.S.C. 103(a) of the other invention.

3. Applicant is reminded that upon the cancellation of claims to a non-elected invention, the

inventorship must be amended in compliance with 37 CFR 1.48(b) if one of the currently named

inventors is no longer an inventor of at least one claim remaining in the application. Any

amendment of inventorship must be accompanied by a request under 37 CFR 1.48(b) and by the

fee under 37 CFR 1.17(i).

Conclusion

4. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Monica Lewis whose telephone number is 571-272-1838.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor,

Zandra Smith can be reached on 571-272-2429. The fax phone number for the organization

where this application or proceeding is assigned is 571-273-8300 for regular and after final

communications.

ML

April 25, 2007

PRIMARY PATENT EXAMINER

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